

Silicon NPN Power Transistors

2SC1617

DESCRIPTION

- With TO-3 package
- High voltage: $V_{CBO(min)}$:300V
- Wide safe oprating area

APPLICATIONS

- For B/W white TV horizontal output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

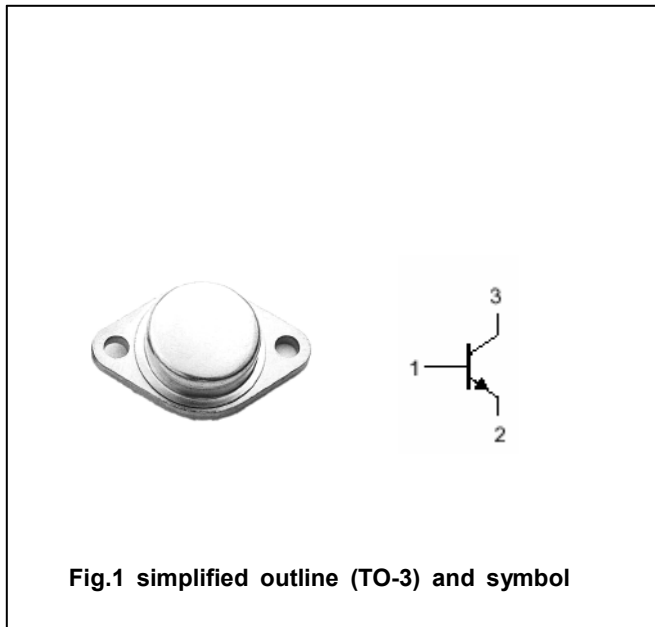


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		7	A
I_E	Emitter current		-7	A
P_C	Collector power dissipation	$T_C=25^\circ C$	50	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5 A			1.2	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =0.5 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =250V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =1A; V _{CE} =5V	30		150	
h _{FE-2}	DC current gain	I _C =7A; V _{CE} =5V	15			
f _T	Transition frequency	I _C =0.5A; V _{CE} =5V		10		MHz

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PACKAGE OUTLINE

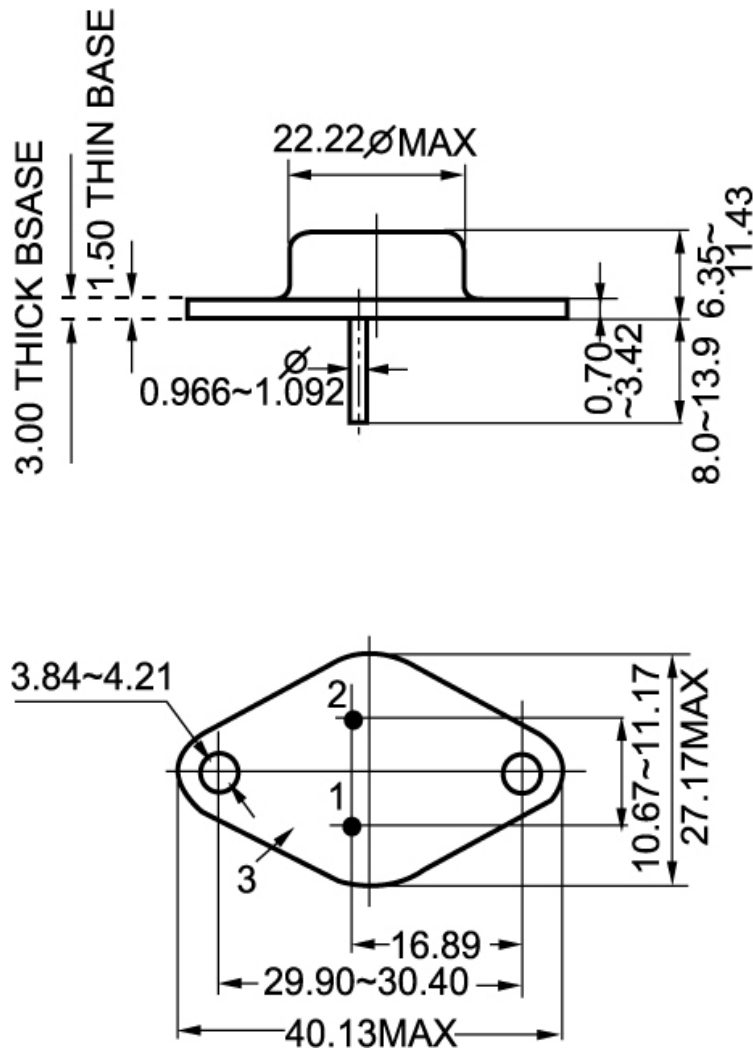


Fig.2 Outline dimensions